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ERRATA

F-Center Gap Mode in Alkali Halides. A Molecular Model, R. S. Singh and S. S. Mitra [Phys. Rev. B 2, 1070 (1970)]. Dr. D. Bäuerle has brought to our attention certain misinterpretations of his results. The sentences starting from line 3 and ending in line 16 of the second paragraph of p. 1072 should accordingly be changed to "... For the F center in KI, a sharp band at 83 cm^{-1} has been observed[1] in the far-infrared absorption. Clearly this should be compared with the calculated frequency of 81.2 cm^{-1} (F_{1u}''). More recently Bäuerle and Hübner [Phys. Rev. B 2, 4252 (1970)] have reported the observation of a gap mode due to an F center in KBr at 99.6 cm^{-1} (1.2 °K). This compares well with our calculated value of 92.6 cm^{-1} (300 °K) for this center. A resonant-band mode peaking around 62 cm^{-1} has been reported[6,14] for the KI:H$^-$ system."

Nonresonant Interband Faraday Rotation in Silicon, Cedric J. Gabriel [Phys. Rev. B 2, 1812 (1970)]. A printer's error was made in Eq. (3). The correct form of the equation is

$$2\gamma=[\xi(-)-\xi(+)]\left(\frac{d\xi(\pm)}{d\alpha}\right)^{-1} .$$

High-Temperature Measurements of the Electron Hall Mobility in the Alkali Halides, C. H. Seager and David Emin [Phys. Rev. B 2, 3421 (1970)]. To correct for an error which has been discovered in the calibration procedure of the apparatus, the quoted Hall mobilities for all samples measured should be multiplied by a factor of 1.24 to obtain the proper values. This correction in no way affects the conclusion drawn by the authors that continuum polaron theories are inadequate in their predictions of the temperature dependence of the data.

Lattice-Dynamical Theory of the Diffusion Process. I. Isotope Effect in Cubic Metals, B. N. Narahari Achar [Phys. Rev. B 2, 3848 (1970)]. The $3N$ normal modes of the lattice perturbed by an isotopic impurity should be labeled by a single index f, rather than the symbols $(\vec{q}, \lambda)$. Accordingly, the symbols $(\vec{q}, \lambda)$ should be replaced by f in the following: (i) Line above Eq. (10), p. 3850. (ii) Equations (10) and (11), p. 3850. (iii) Line 3 from top of the right-hand column, p. 3850.

Ionic Raman Effect. I. Scattering by Localized Vibration Modes, A. A. Maradudin and R. F. Wallis [Phys. Rev. B 2, 4294 (1970)]. An unfortunate numerical error occurred in plotting Figs. 1 and 2 on the basis of Eqs. (17) and (29), respectively. The scattering efficiencies shown in these figures are consequently too large by factors of 10^3–10^4. The corrected results, together with a demonstration that the ionic Raman effect for the system $\text{CaF}_2:\text{H}^-$ dominates the electronic Raman effect when the incident light is in the infrared, are presented in a paper by L. B. Humphreys, A. A. Maradudin, and R. F. Wallis to appear in *Physics of Impurity Centres in Crystals* (Academy of Sciences of the Estonian S.S.R., Tartu, 1971).

Electromodulation of the Optical Properties of Thallium-Activated Potassium Bromide, U. Giorgianni, V. Grasso, and G. Saitta [Phys. Rev. B 2, 5007 (1970)]. Figures 1 and 2 should be interchanged, however, the figure captions are correctly numbered.

Intrinsic Diffusion of Boron and Phosphorus in Silicon Free from Surface Effects, R. N. Ghoshtagore [Phys. Rev. B 3, 389 (1971)]. Typesetting errors occurred in the third and fourth sentences of the abstract during the galley-correcting process. The correct abstract is as follows.

Boron and phosphorus were diffused in either hydrogen or pure-argon atmosphere into float-zoned, epitaxial, and oxygen-doped (111) silicon from a 4–12-μ-thick epitaxial-doped silicon surface layer. Under intrinsic conditions, the concentration profiles obtained show Fickian behavior at all surface and bulk concentration conditions. Between 1130 and 1405 °C, the intrinsic diffusivities can be described by $D_P = 7.4 \times 10^{-2} \exp[(-3.30 \pm 0.03 \text{ eV})/kT]$ cm^2/sec and $D_B = 2.1 \times 10^{-3} \exp[(-2.85 \pm 0.05 \text{ eV})/kT]$ cm^2/sec. Compared with earlier studies using oxide diffusion sources, the diffusion coefficients of both boron and phosphorus are found to be considerably smaller. Moreover, above 1130 °C they are independent of surface concentration ($\leqslant 3 \times 10^{19}$ cm^{-3}), bulk conductivity type (n or p) and level (6×10^{13}–8×10^{18} cm^{-3}), surface-to-bulk concentration ratio (~ 1–3.3×10^5), and oxygen concentration (to 10^{18} cm^{-3}). In the light of some related work, the present results are shown to indicate the true bulk-diffusion process in silicon.